Superior High Intensity for High Voltage System

Acrich MJT – 3030 series \$1WM-3030xx8006-00000000-00001 (Cool, Neutral, Warm)





Product Brief

Description

- This White Colored surface-mount LED comes in standard package dimension. Package Size: 3.0x3.0x0.6mm
- The MJT series of LEDs are designed for AC & DC(High Voltage) operation and high Intensity output applications
- The MJT is ideal light sources for general illumination applications and custom designed solutions
- The package design coupled with careful selection of component materials allow these products to perform with high reliability

Features and Benefits

- High Intensity output and high luminance
- Designed for high voltage operation
- Compact size package
- SMT solderable
- High Color Quality with CRI Min.80(R9>0)
- RoHS compliant

Key Applications

- General lighting
- Replacement lamps
- Architectural
- Commercial

Table 1. Product Selection Table

Deference Code	Calar	Nominal	Davi Niverban	CRI
Reference Code	Reference Code Color		Part Number	Min
		6500K	S1WM-3030658006-00000000-00001	
SAW8C22B-IZ Neutra White	Cool White	5700K	S1WM-3030578006-00000000-00001	
		5000K	S1WM-3030508006-00000000-00001	
	Neutral White	4000K	S1WM-3030408006-00000000-00001	80
		3500K	S1WM-3030358006-00000000-00001	
	Warm White	3000K	S1WM-3030308006-00000000-00001	
		2700K	S1WM-3030278006-00000000-00001	



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Performance Characteristics

Table 2. Product Selection Guide, $I_F = 150mA$, $T_j = 25^{\circ}C$, RH30%

Min. CRI, R _a ^[4]	Nominal CCT [K] ^[1]	Min. Flux [lm]	Typ. Luminous Flux Φ _V ^[3] [lm] @150mA	Typ. Luminous Efficacy [lm/W] @150mA	Part Number
	6500	130.2	141.1	154	S1WM-3030658006- 00000000-00001
	5700	136.4	141.1	154	S1WM-3030578006- 00000000-00001
	5000	136.4	142.0	155	S1WM-3030508006- 00000000-00001
80	4000	135.5	141.2	154	S1WM-3030408006- 00000000-00001
	3500	134.2	138.8	152	S1WM-3030358006- 00000000-00001
	3000	128.1	135.7	148	S1WM-3030308006- 00000000-00001
	2700	128.1	135.1	148	S1WM-3030278006- 00000000-00001

Notes:

- (1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (2) Seoul Semiconductor maintains a tolerance of $\pm 7\%$ on Intensity and power measurements. The luminous intensity Iv was measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package.
- (3) The lumen table is only for reference.

Performance Characteristics

Table 3. Characteristics, I_F=150mA, T_i= 25°C, RH30%

Parameter	Symbol	Value			Unit
Faranietei	Symbol	Min.	Тур.	Max.	Onit
Forward Current	I _F	-	150	250	mA
Forward Voltage	V_{F}	-	6.2	6.4	V
CRI [3]	R _a	80	-	-	Deg.
Viewing Angle	2Θ _{1/2}	-	120	-	Deg.
Storage Temperature	T_{stg}	- 40	-	+ 100	°C
Thermal resistance (J to S) [4]	$R\theta_{J-S}$	-	11	17	°C/W
ESD Sensitivity(HBM)	-	Class 3A JEDEC JS-001-2017			

Table 4. Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Forward Current	l _F	250	mA
Power Dissipation	P_{D}	1.5	W
Junction Temperature	T _j	125	°C
Operating Temperature	T _{opr}	-40 ~ + 100	°C
Storage Temperature	T _{stg}	-40 ~ + 100	°C

Notes:

- (1) Seoul Semiconductor maintains a tolerance of $\pm 7\%$ on Intensity and power measurements.
- (2) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.

Color coordinate: ±0.005, CCT ±5% tolerance.

- (3) Tolerance is ±2.0 on CRI measurements.
- (4) Thermal resistance: Rth_{JS} (Junction to Solder)

Fig 1. Color Spectrum, T_i = 25°C, I_F=150mA

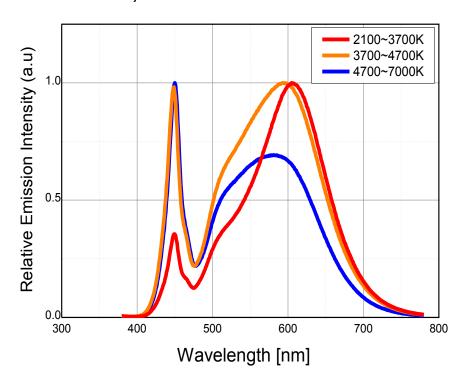


Fig 2. Radiant Pattern, T_i = 25°C, I_F=150mA

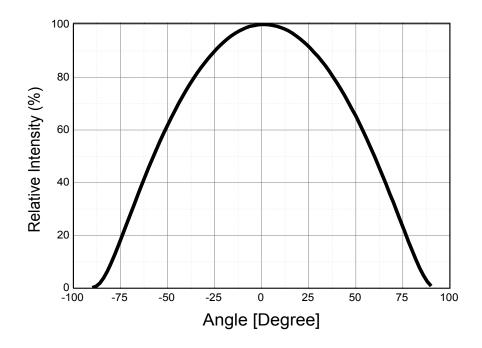


Fig 3. Forward Voltage vs. Forward Current, T_i = 25°C

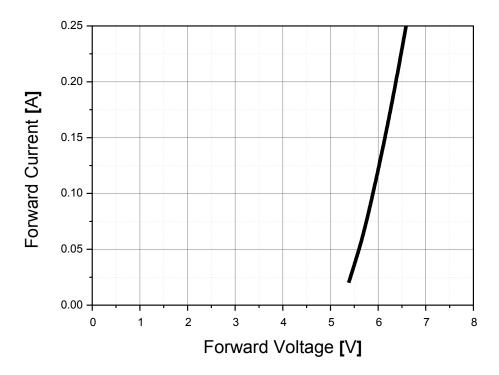


Fig 4. Forward Current vs. Relative Luminous Intensity, T_i = 25°C

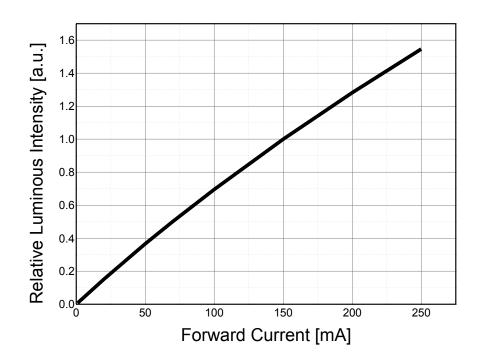
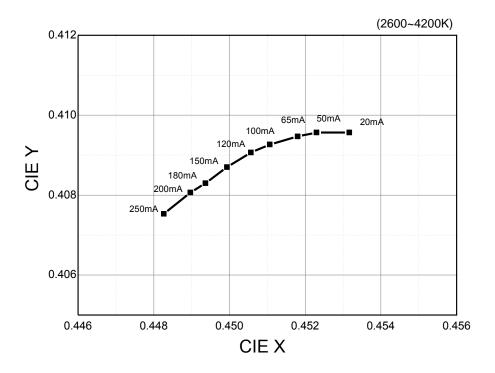


Fig 5. Forward Current vs. CIE X,Y Shift, T_i = 25°C



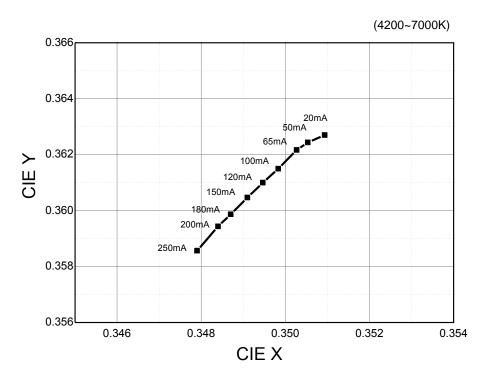


Fig 6. Junction Temperature vs. Relative Luminous Intensity, I_F=150mA

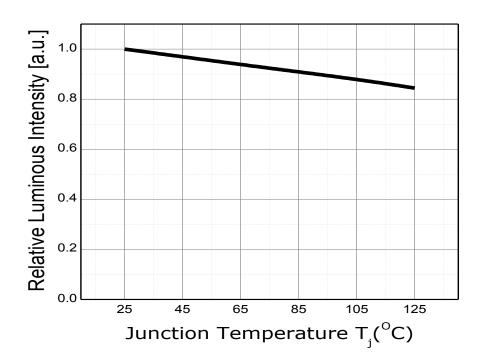


Fig 7. Junction Temperature vs. Relative Forward Voltage, I_F=150mA

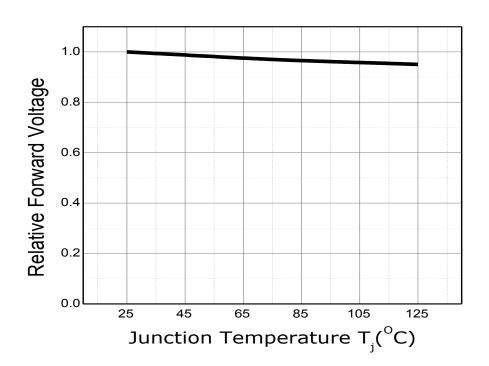
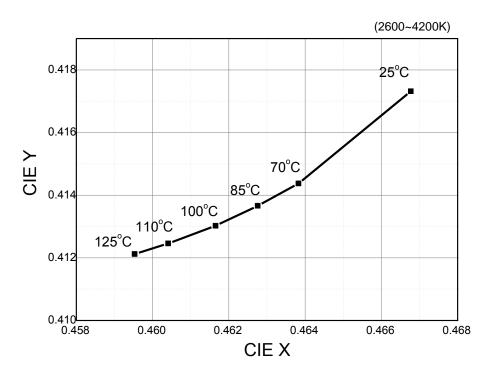


Fig 8. Chromaticity Coordinate vs. Junction Temperature, I_F=150mA



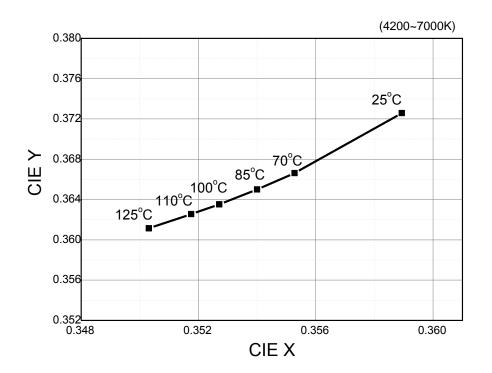
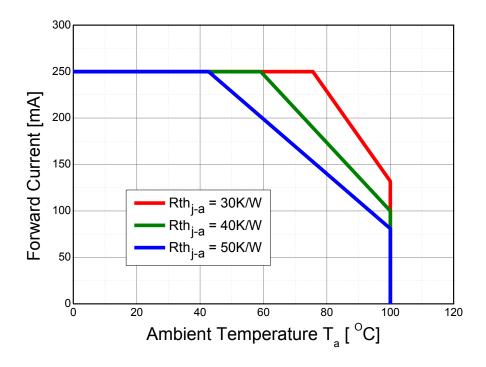


Fig 9. Ambient Temperature vs. Maximum Forward Current, $T_{j_max} = 125^{\circ}C$



Color Bin Structure

Table 5. Bin Code description, $T_j=25$ °C, $I_F=150$ mA

Part Number	Luminous Flux (lm) @5000K		Color Chromaticity	Typical F	orward Vo	oltage (V)	
Part Number	Bin Code	Min.	Max.	Coordinate	Bin Code	Min.	Max.
	M42	130	136	Defer to page 42, 44	Z58	5.8	6.0
S1W0- 3030xx8003-	M44	136	140		Z60	6.0	6.2
00000000-00004	M45	140	143	Refer to page.12~14	Z62	6.2	6.4
	M46	143	155	-			

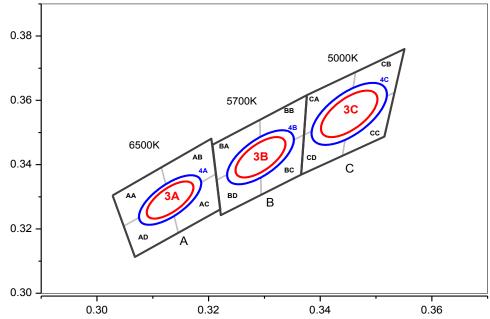
Table 6. Intensity rank distribution

Available ranks

сст	CIE		IV F	Rank	
6000- 7000K	А	M42	M44	M45	M46
5300- 6000K	В	M42	M44	M45	M46
4700 ~ 5300K	С	M42	M44	M45	M46
3700 ~ 4200K	E	M42	M44	M45	M46
3200 ~ 3700K	F	M42	M44	M45	M46
2900 ~ 3200K	G	M42	M44	M45	M46
2600 ~ 2900K	Н	M42	M44	M45	M46

Color Bin Structure

CIE Chromaticity Diagram (Cool white), T_i=25°C, I_F=100mA



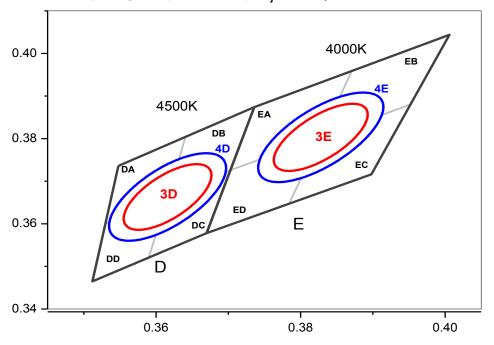
6500K 3Step		5700	K 3Step	5000K 3Step		
	3A	3B 3C			3C	
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.0066	Major Axis a	0.0071	Major Axis a	0.0081	
Minor Axis b	0.0027	Minor Axis b	0.0030	Minor Axis b	0.0035	
Ellipse	58	Ellipse	59	Ellipse	60	
Rotation Angle	30	Rotation Angle	otation Angle		00	

6500K 4Step		5700	K 4Step	5000K 4Step		
	4A		4B		4C	
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.0088	Major Axis a	0.0095	Major Axis a	0.0108	
Minor Axis b	0.0036	Minor Axis b	0.0040	Minor Axis b	0.0047	
Ellipse	58	Ellipse	59	Ellipse	60	
Rotation Angle	50	Rotation Angle	39	Rotation Angle	00	

Α	A	А	В	Α	С	А	D
CIE X	CIE Y						
0.3028	0.3304	0.3115	0.3393	0.3131	0.329	0.3048	0.3209
0.3048	0.3209	0.3131	0.329	0.3146	0.3187	0.3068	0.3113
0.3131	0.329	0.3213	0.3371	0.3221	0.3261	0.3146	0.3187
0.3115	0.3393	0.3205	0.3481	0.3213	0.3371	0.3131	0.329
В	A	В	В	В	C	В	D
CIE X	CIE Y						
0.3207	0.3462	0.3292	0.3539	0.3293	0.3423	0.3215	0.3353
0.3215	0.3353	0.3293	0.3423	0.3294	0.3306	0.3222	0.3243
0.3293	0.3423	0.3371	0.3493	0.3366	0.3369	0.3294	0.3306
0.3292	0.3539	0.3376	0.3616	0.3371	0.3493	0.3293	0.3423
С	A	c	В	C	C	С	D
CIE X	CIE Y						
0.3376	0.3616	0.3463	0.3687	0.3452	0.3558	0.3371	0.3493
0.3371	0.3493	0.3452	0.3558	0.344	0.3428	0.3366	0.3369
0.3452	0.3558	0.3533	0.3624	0.3514	0.3487	0.344	0.3428
0.3463	0.3687	0.3551	0.376	0.3533	0.3624	0.3452	0.3558

Color Bin Structure

CIE Chromaticity Diagram (Cool white), T_i=25°C, I_F=100mA



4500K 3Step					
3D					
Center point	0.3611 : 0.3658				
Major Axis a	0.0090				
Minor Axis b	0.0039				
Ellipse Rotation Angle	55				

4000K 3Step						
3E						
Center point	0.3818 : 0.3797					
Major Axis a	0.0094					
Minor Axis b	0.0040					
Ellipse Rotation Angle	53					

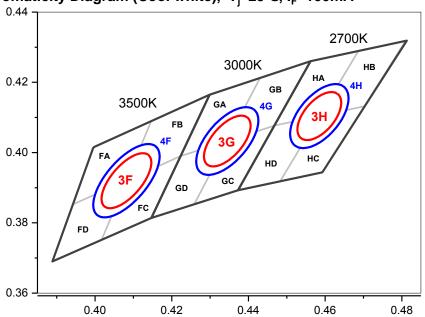
4500K 4Step					
4D					
Center point	0.3611 : 0.3658				
Major Axis a	0.0120				
Minor Axis b	0.0052				
Ellipse	EE				
Rotation Angle 55					

4000K 4Step				
4E				
Center point	0.3818 : 0.3797			
Major Axis a	0.0125			
Minor Axis b	0.0053			
Ellipse	53			
Rotation Angle	53			

D)A	D	В	D	С	D	D
CIE X	CIE Y						
0.3548	0.3736	0.3641	0.3804	0.3616	0.3663	0.353	0.3601
0.353	0.3601	0.3616	0.3663	0.359	0.3521	0.3511	0.3465
0.3616	0.3663	0.3703	0.3726	0.367	0.3578	0.359	0.3521
0.3641	0.3804	0.3736	0.3874	0.3703	0.3726	0.3616	0.3663
E	A	Е	В	Е	С	E	D
CIE X	CIE Y	CIE X	B CIE Y	CIE X	C CIE Y	CIE X	D CIE Y
CIE X	CIE Y						
CIE X 0.3736	CIE Y 0.3874	CIE X 0.3871	CIE Y 0.3959	CIE X 0.3828	CIE Y 0.3803	CIE X 0.3703	CIE Y 0.3726

Color Bin Structure

CIE Chromaticity Diagram (Cool white), $T_j=25$ °C, $I_F=100$ mA

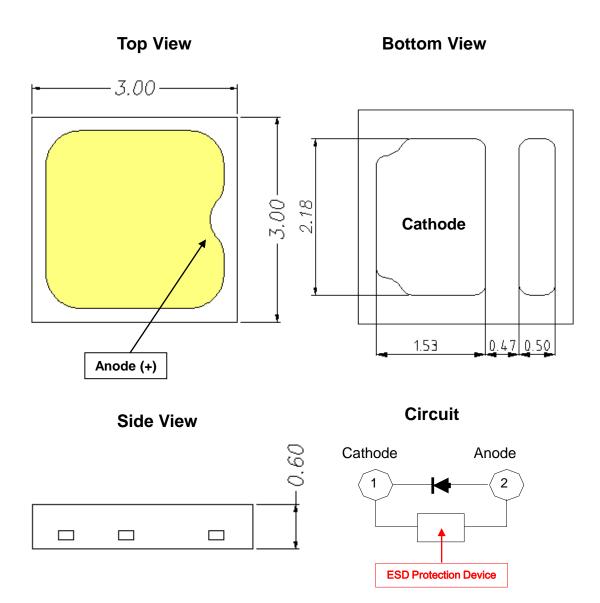


3500K 3Step		3000K 3Step		2700K 3Step	
3	Step	3 Step		3 Step	
Center point	0.4073 : 0.3917	Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101
Major Axis a	0.0093	Major Axis a	0.0085	Major Axis a	0.0079
Minor Axis b	0.0041	Minor Axis b	0.0041	Minor Axis b	0.0041
Ellipse	53	Ellipse	53	Ellipse	 54
Rotation Angle	55	Rotation Angle	55	Rotation Angle	J 4

	K 4Step	3000K 4Step		2700K 4Step		
4 Step		4 Step		4 Step		
Center point	0.4073 : 0.3917	Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101	
Major Axis a	0.0124	Major Axis a	0.0113	Major Axis a	0.0105	
Minor Axis b	0.0055	Minor Axis b	0.0055	Minor Axis b	0.0055	
Ellipse	53	Ellipse	53	Ellipse	54	

	FA	F	В	F	С	F	D
CIE X	CIE Y						
0.3996	0.4015	0.4146	0.4089	0.4082	0.392	0.3943	0.3853
0.3943	0.3853	0.4082	0.392	0.4017	0.3751	0.3889	0.369
0.4082	0.392	0.4223	0.399	0.4147	0.3814	0.4017	0.3751
0.4146	0.4089	0.4299	0.4165	0.4223	0.399	0.4082	0.392
	GA	G	В	G	C	G	D
CIE X	CIE Y						
0.4299	0.4165	0.443	0.4212	0.4345	0.4033	0.4223	0.399
0.4223	0.399	0.4345	0.4033	0.4259	0.3853	0.4147	0.3814
0.4345	0.4033	0.4468	0.4077	0.4373	0.3893	0.4259	0.3853
0.443	0.4212	0.4562	0.426	0.4468	0.4077	0.4345	0.4033
	HA	Н	В	н	c	H	D
CIE X	CIE Y						
0.4562	0.426	0.4687	0.4289	0.4585	0.4104	0.4468	0.4077
0.4468	0.4077	0.4585	0.4104	0.4483	0.3919	0.4373	0.3893
0.4585	0.4104	0.4703	0.4132	0.4593	0.3944	0.4483	0.3919
0.4687	0.4289	0.481	0.4319	0.4703	0.4132	0.4585	0.4104

Mechanical Dimensions



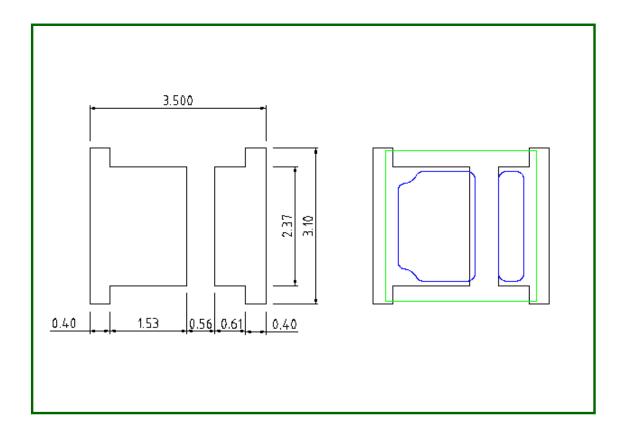
Notes:

(1) All dimensions are in millimeters.

(2) Scale: none

(3) Undefined tolerance is $\pm 0.2 mm$

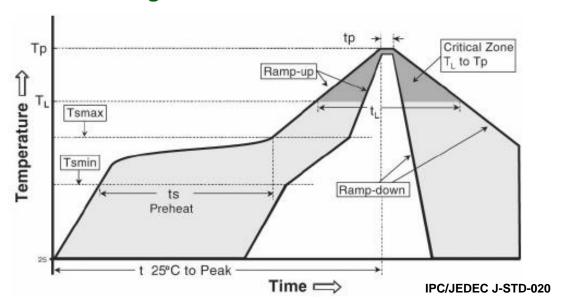
Recommended Solder Pad



Notes:

- (1) All dimensions are in millimeters.
- (2) Scale: none
- (3) This drawing without tolerances are for reference only
- (4) Undefined tolerance is ± 0.1 mm
- (5) The appearance and specifications of the product may be changed for improvement without notice.

Reflow Soldering Characteristics

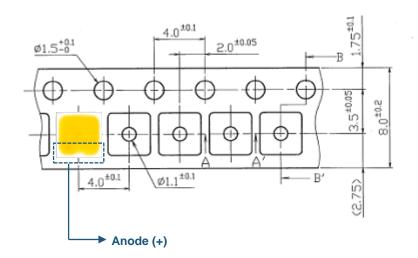


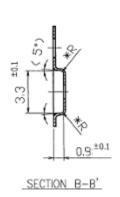
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _{s_max} to T _p)	3° C/second max.	3° C/second max.
$ \begin{array}{c} \textbf{Preheat} \\ \textbf{-} \textbf{ Temperature Min } (\textbf{T}_{\textbf{s_min}}) \\ \textbf{-} \textbf{ Temperature Max } (\textbf{T}_{\textbf{s_max}}) \\ \textbf{-} \textbf{ Time } (\textbf{T}_{\textbf{s_min}} \textbf{ to } \textbf{T}_{\textbf{s_max}}) (\textbf{t}_{\textbf{s}}) \\ \end{array} $	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-180 seconds
Time maintained above: - Temperature (T _L) - Time (t _L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak Temperature (T _p)	215℃	260℃
Time within 5°C of actual Peak Temperature (t _p)2	10-30 seconds	20-40 seconds
Ramp-down Rate	6 °C/second max.	6 °C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

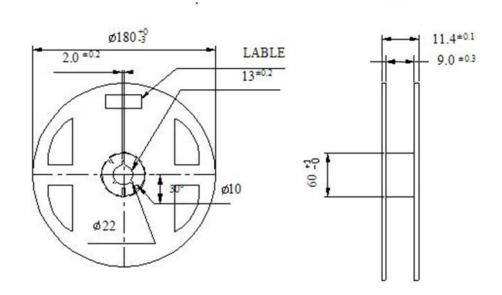
Caution:

- (1) Reflow soldering is recommended not to be done more than two times
 In the case of more than 24 hours passed soldering after first, LEDs will be damaged.
- (2) Repairs should not be done after the LEDs have been soldered When repair is unavoidable, suitable tools must be used.
- (3) When soldering, do not put stress on the LEDs during heating.
- (4) After soldering, do not warp the circuit board.

Emitter Tape & Reel Packaging







(Tolerance: ± 0.2 , Unit: mm)

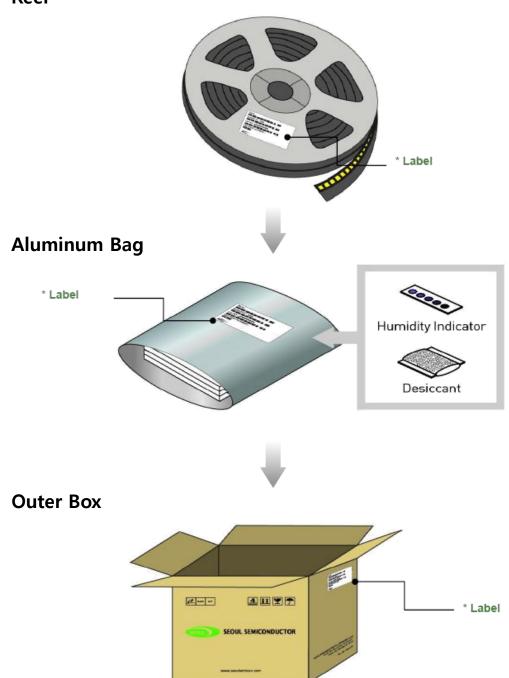
Notes:

- (1) Quantity: Max 4,500pcs/Reel
- (2) Cumulative Tolerance : Cumulative Tolerance/10 pitches to be ± 0.2 mm
- (3) Adhesion Strength of Cover Tape

 Adhesion strength to be 0.1-0.7N when the cover tape is turned off from the carrier tape at the angle of 10° to the carrier tape.
- (4) Package: P/N, Manufacturing data Code No. and Quantity to be indicated on a damp proof Package.

Emitter Tape & Reel Packaging

Reel



Product Nomenclature

Table 7. Part Numbering System:

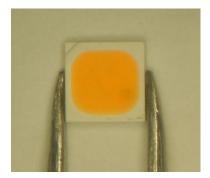
Part Number Code	Description	Part Number	Value
X ₁	Company	S	Seoul Semiconductor
X ₂	Level of Integration	1	Discrete LED
X ₃ X ₄	Technology	WM	MJT White
$X_5X_6X_7X_8$	Dimension	3030	
X ₉ X ₁₀	CCT	xx	
X ₁₁ X ₁₂	CRI	80	
X ₁₃ X ₁₄	Vf	06	
X ₁₅ X ₁₆ X ₁₇	Characteristic code Flux Rank	000	
X ₁₈ X ₁₉ X ₂₀	Characteristic code Vf Rank	000	
X ₂₁ X ₂₂	Characteristic code Color Step	00	
X ₂₃ X ₂₄	Туре	00	
X ₂₅ X ₂₆ X ₂₇	Internal code	001	

Handling of Silicone Resin for LEDs

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



- (3) When populating boards in SMT production, there are basically no restrictions regarding the form of the pick and place nozzle, except that mechanical pressure on the surface of the resin must be prevented. This is assured by choosing a pick and place nozzle which is larger than the LED's reflector area.
- (4) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust.

As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of components.

- (5) SSC suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.

 Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.
- (6) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this. product with acid or sulfur material in sealed space.

Precaution for Use

(1) Storage

To avoid the moisture penetration, we recommend store in a dry box with a desiccant. The recommended storage temperature range is 5°C to 30°C and a maximum humidity of RH50%.

(2) Use Precaution after Opening the Packaging

Use proper SMT techniques when the LED is to be soldered dipped as separation of the lens may affect the light output efficiency.

Pay attention to the following:

- a. Recommend conditions after opening the package
 - Sealing
 - Temperature : 5 ~ 30°C Humidity : less than RH60%
- b. If the package has been opened more than 4 week(MSL_2a) or the color of the desiccant changes, components should be dried for 10-24hr at 65±5°C
- (3) Do not apply mechanical force or excess vibration during the cooling process to normal temperature after soldering.
- (4) Do not rapidly cool device after soldering.
- (5) Components should not be mounted on warped (non coplanar) portion of PCB.
- (6) Radioactive exposure is not considered for the products listed here in.
- (7) Gallium arsenide is used in some of the products listed in this publication.
 These products are dangerous if they are burned or shredded in the process of disposal.
 It is also dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.
- (8) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.
- (9) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.

Precaution for Use

- (10) The appearance and specifications of the product may be modified for improvement without notice.
- (11) Long time exposure of sunlight or occasional UV exposure will cause lens discoloration.
- (12) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.
- (13) Attaching LEDs, do not use adhesives that outgas organic vapor.
- (14) The driving circuit must be designed to allow forward voltage only when it is ON or OFF.
 If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.
- (15) Similar to most Solid state devices;
 LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS).
 Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.
- a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event. One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

Environmental controls:

- Humidity control (ESD gets worse in a dry environment)

Precaution for Use

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
 (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.
- c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:
 - A surge protection circuit
 - An appropriately rated over voltage protection device
 - A current limiting device

Company Information

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Company Information

Seoul Semiconductor (www.SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, Home appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs.

The company's broad product portfolio includes a wide array of package and device choices such as Acrich and Acirch2, high-brightness LEDs, mid-power LEDs, side-view LEDs, and through-hole type LEDs as well as custom modules, displays, and sensors.

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